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Sheet 1 of 1

Form 1449*	Atty. Docket No.: 303.466US1	Serial No. 09/069,668
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Kie Y. Ahn et al.	
	Filing Date: April 29, 1998	Group: 2814

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes / No
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Initial	Hamakawa, Y., et al., "Optoelectronics and Photovoltaic Applications of Microcrystalline SiC", <u>Materials Research Society Symposium Proceedings</u> , 164, Boston, MA, 291-301, (11/29-12/1, 1989)
Initial	Mohajerzadeh, S., et al., "A Low Energy Ion Beam Assisted Deposition Technique for Realizaing iso-type SiGe/Si hetero-interface diodes", <u>Thin Solid Films</u> , 283, 182-187, (1996)
Initial	Mohajerzadeh, S., et al., "A Low-Temperature Ion Vapor Deposition Technique for Silicon and Silicon-Germanium Epitaxy", <u>Canadian J. Physics</u> , 74, S69-S73, (1996)
Initial	Mohri, M., et al., "Effect of SiF(4)/SiH(4)/H(2) Flow Rates on Film Properties of Low-Temperature Polycrystalline Silicon Films Prepared by Plasma Enhanced Chemical Vapor Deposition", <u>IEICE Transactions on Electronics</u> , E77-C, 1677-1684, (Oct. 1994)

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Examiner <i>William D. Patel</i>	Date Considered 13 JANUARY 2000
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Examiner <i>Miller D. J. Col</i>	Date Considered 13 JANUARY 2000
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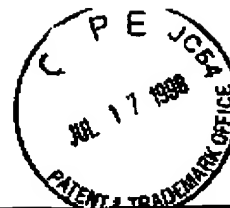
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